NSN 5962-01-408-0768

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Maximum Power Dissipation Rating:
1.5 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Milstar
Features Provided:
Burn in, mil-std-883, class b and electrostatic sensitive and radiation hardened and selected item and tested to mil-std-883 and w/reset and
frequency compensated
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Input Circuit Pattern:
32 input
Criticality Code Justification:
Cbbl
Current Rating Per Characteristic:
-10.00 milliamperes collector cutoff current, dc, with specified resistance between base and emitter microamperes and 10.00 milliamperes
reverse current, dc microamperes
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital, microcontroller
Voltage Rating And Type Per Characteristic:
4.0 volts power source and 6.0 volts power source and -0.5 volts input and 6.5 volts input
Memory Device Type:
Ram
Special Features:
Device is a cmos, 8-bit microcontroller with 256 x 8 ram; this is a selected item made from rc351-3816-012 which is made from
351-3816-012 which is a 1ch66 80c32/bqa (signetics); case outline designator gdip1-t40 or cdip2-t40 as designated in mil-std-1835; oscillator
frequency is from 3.5 to 12.0 mhz

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

40 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Domilitarization.

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